

High Power Laser Diode Chip on Carrier



Part Number: COC-266

High Power Triple Junction Chip on Carriers
Multi-Mode Fabry-Perot
Pulsed Wavelength at 1550nm



Features

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard Chip on Carrier
- Cost Effective

Application

- ToF LiDAR for Automotive and Drones
- Laser Rangefinders
- Target Illumination
- Aerospace



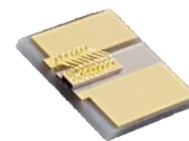
SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

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Specification

COC-266



Optical	Symbol	Typ.	Units
Center Wavelength	λ_c	1550	nm (± 20)
Output Power (<10ns)*	P_{out}	80	watts ($\pm 10\%$)
Output Power (150ns)*	P_{out}	52	watts ($\pm 10\%$)
Emitter Width	W	180	μm
Spectral Width FWHM	$\Delta\lambda$	22	nm
Slope Efficiency	η	0.9	W/A
Fast Axis Div.	θ_{\perp}	28	deg FWHM
Slow Axis Div.	θ_{\parallel}	12	deg FWHM
Electrical	Symbol		Units
Power Conversion Eff.	η	8	%
Operating Current (<10ns)	I_{op}	90	A
Operating Current (<150ns)	I_{op}	56	A
Threshold Current	I_{TH}	1	A
Operating Voltage	V_{op}	11	V
Duty Cycle	DC	0.1	%
Mechanical		Range	Units
Operating Temp.**		-40 to 85	$^{\circ}C$
Storage Temp.		-40 to 85	$^{\circ}C$

*Specified values are rated at a constant heat sink temperature of 20°C.

**High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.

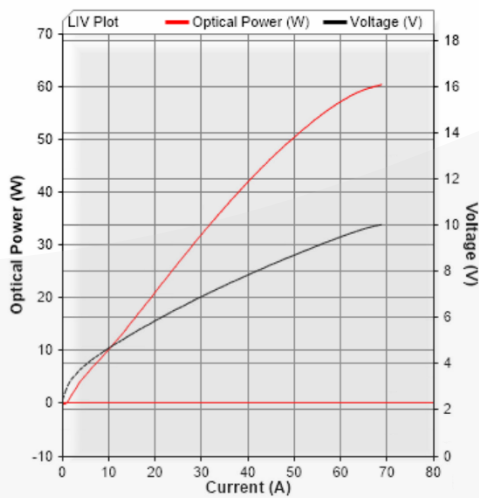
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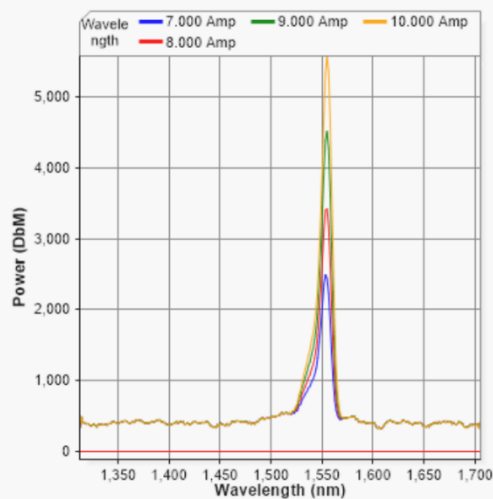
SemiNex Laser Diodes COC-266

Graphs & Data

Typical COC L-I-V Characteristics



Typical COC Output Spectrum

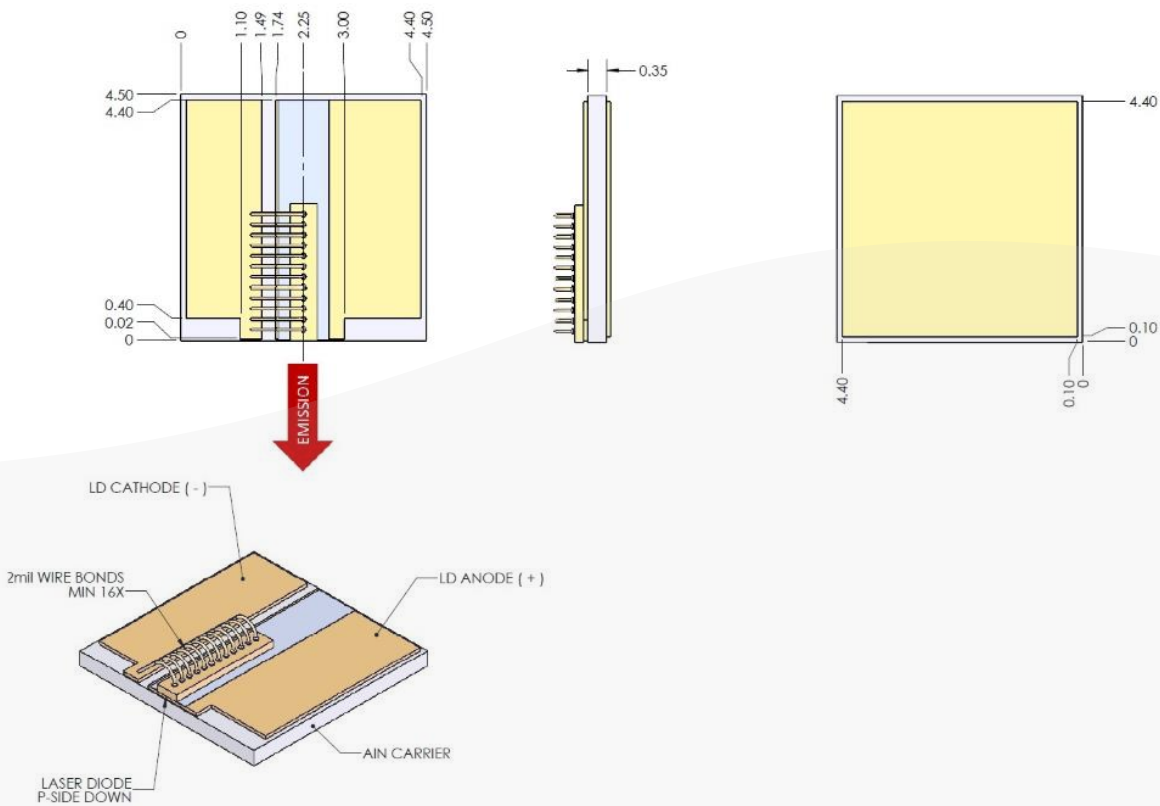
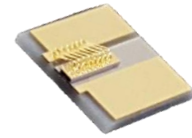


*Tested with 150nsec pulse @ 0.1% Duty Cycle

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Mechanical Drawing



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